Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	517	semiconductor and active adj2 (region pattern) with amorphous adj2 silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:07
L2	1816	349/43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:06
L3	32	2 and 1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:10
L4	2674	semiconductor and active adj2 (region pattern layer) with amorphous adj2 silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:26
L5	2309	semiconductor and active adj2 (pattern layer) with amorphous adj2 silicon	US-PGPUB; USPAT; USÖCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:07
L6	243	2 and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:08
. L7 .*	2	"6580473".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:11
L8	2	"6262784".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:12

L9	2	"5696566".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB -	OR .	ON	2005/11/01 09:15
L10		9 and amorphous	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:14
L11	1	8 and amorphous adj2 silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:14
L12	2	"5517341".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR -	ON	2005/11/01 09:15
L13	5174622	semiconductor and active adj2 (region pattern layer) with amorphous adj2 silicon and peripheral (region area)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:28
L14	195	semiconductor and active adj2 (region pattern layer) with amorphous adj2 silicon and peripheral adj2 (region area)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11:32
L15	27	2 and 14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:55
L16	85	14 and polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 10:06

L17	110	14 not 16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/11/01 10:07
L18	14	2 and 17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 09:55
L19	154	14 and (polysilicon poly?Si crystalliz\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11:16
L20	41	14 not 19	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	ON	2005/11/01 11:14
ef.	· ·		DERWENT; IBM_TDB			
L21	94	14 and (polysilicon poly?Si poly adj crystalliz\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11:17
L22	457	349/151	US-PGPUB; USPAT; USOCR;	OR	ON	2005/11/01 11:30
-		÷	EPO; JPO; DERWENT; IBM_TDB		- N	
L23	7	22 and 21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11:29
L24	0	21 not 14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11:27

L25	101	14 not 21	US-PGPUB;	OR	ON	2005/11/01 11:28
223	101	14 1100 21	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11.26
L26	9	22 and 14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11:30
L27	597	349/152	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11:30
L28	5	27 and 14	US-PGPUB; USPAT; USOCR;	OR	ON	2005/11/01 11:31
			EPO; JPO; DERWENT; IBM_TDB			
L29	1024	349/149	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11:31
L30	5	29 and 14	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	ON	2005/11/01 11:31
*	*	-	DERWENT; IBM_TDB	(1- x -	· · · · · · · · · · · · · · · · · · ·	
L31	31	semiconductor and active adj2 (region pattern layer) with amorphous adj2 silicon and peripheral adj2 (region area) with driv\$3 adj2 circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11:34
L32	31	semiconductor and active adj2 (region pattern layer) with amorphous adj2 silicon and peripheral adj2 (region area) with driv\$3 adj2 (circuit transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ΟŇ	2005/11/01 11:38

L33	. 191	semiconductor and active adj2 (region pattern layer) with amorphous adj2 silicon and driv\$3 adj2 transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11:39
L34	4	22 and 33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11:41
L35	14	2 and 33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/01 11:41